

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

BSS138W-TP-MS

Product specification

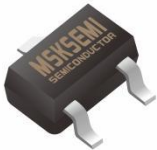
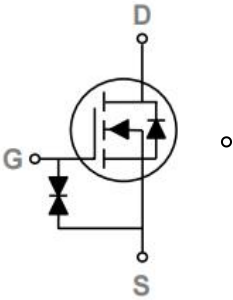
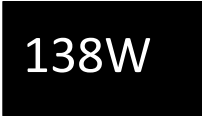
General Features

- 55V,300mA, $R_{DS(ON)} = 1.2\Omega @ V_{GS} = 10V$
- Improved dv/dt capability
- Fast switching
- Green Device Available

Application

- Notebook
- Load Switch
- Battery Protection
- Hand-held Instruments

Reference News

PACKAGE OUTLINE	Pin Configuration	Marking
		
SOT-323		

Absolute Maximum Ratings $T_c=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	55	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_A=25^{\circ}\text{C}$)	300	mA
	Drain Current – Continuous ($T_A=70^{\circ}\text{C}$)	240	mA
I_{DM}	Drain Current – Pulsed ¹	1.2	A
P_D	Power Dissipation ($T_A=25^{\circ}\text{C}$)	313	mW
	Power Dissipation – Derate above 25°C	2.5	$\text{mW}/^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	450	$^{\circ}\text{C}/\text{W}$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$	55	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	0.05	---	$\text{V}/^{\circ}\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=48\text{V}$, $V_{GS}=0\text{V}$, $T_J=25^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=55\text{V}$, $V_{GS}=0\text{V}$, $T_J=85^{\circ}\text{C}$	---	---	400	A
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$	---	---	± 6	μA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V , I _D =0.3A	---	1.2	1.5	Ω
		V _{GS} =4.5V , I _D =0.2A	---	1.5	2.3	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	0.8	1.1	1.6	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	3	---	mV/°C

On Characteristics

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ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	3	---	mV/°C

Dynamic and switching Characteristics

C _{iss}	Input Capacitance	V _{DS} =30V , V _{GS} =0V , F=1MHz	---	23	---	pF
C _{oss}	Output Capacitance		---	16	---	
C _{rss}	Reverse Transfer Capacitance		---	10	---	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V , Force Current	---	---	300	mA
I _{SM}	Pulsed Source Current		---	---	600	mA
V _{SD}	Diode Forward Voltage	V _{GS} =0V , I _S =0.3A , T _J =25°C	---	---	1.4	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2% .
3. Essentially independent of operating temperature.

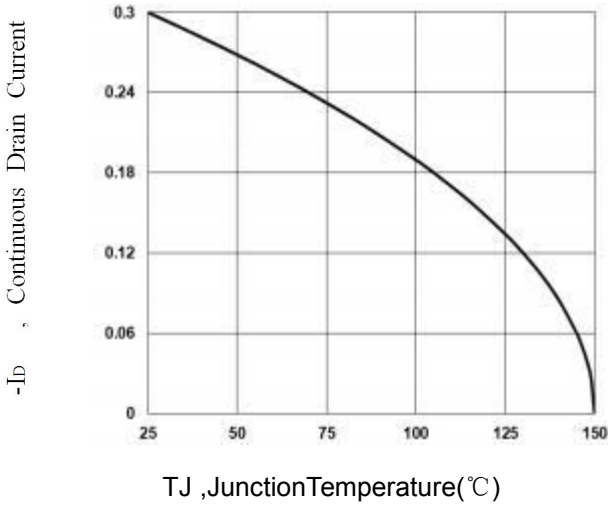


Fig.1 Continuous Drain Current vs. T_C

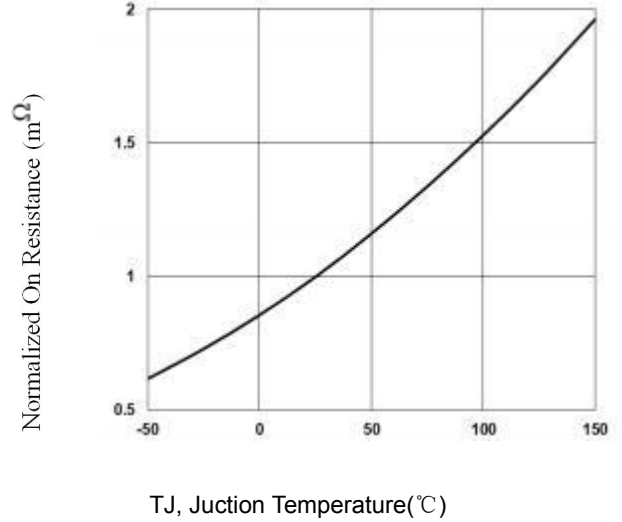


Fig.2 Normalized $R_{DS(on)}$ vs. T_J

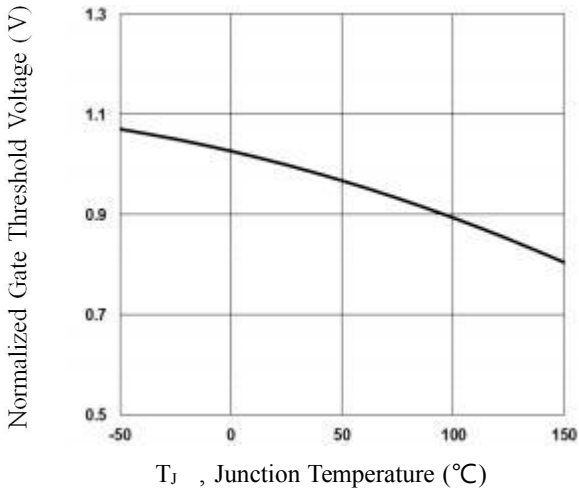


Fig.3 Normalized V_{th} vs. T_J

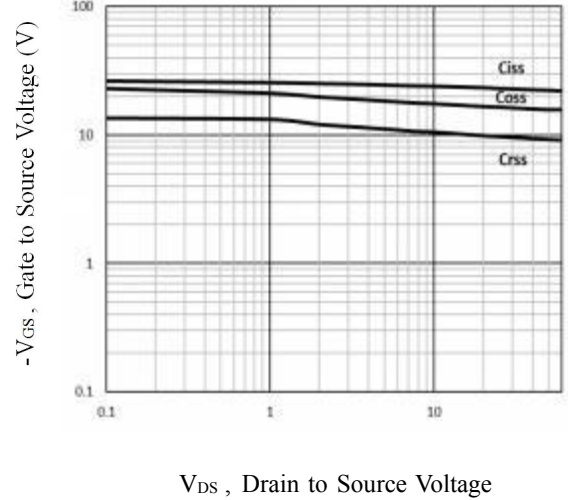


Fig.4 Capacitance Characteristics

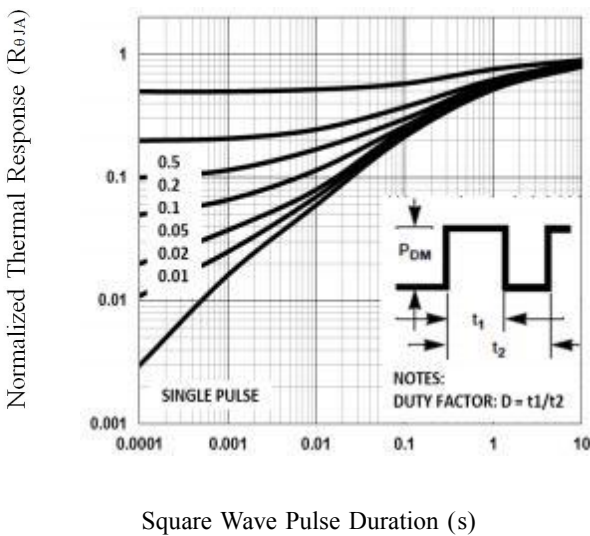


Fig.5 Normalized Transient Response

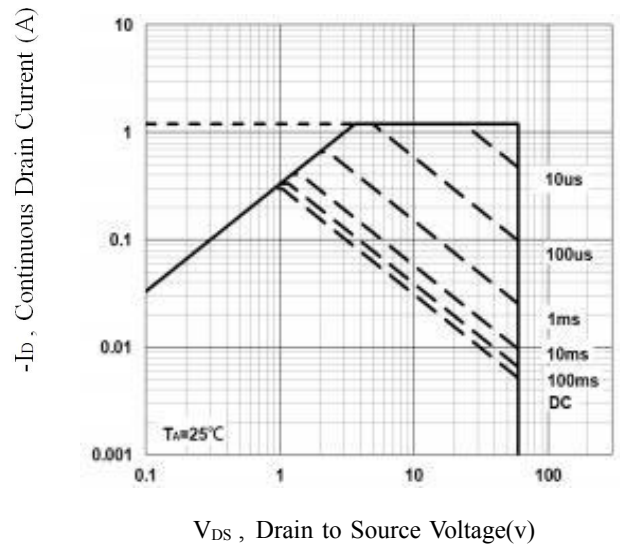
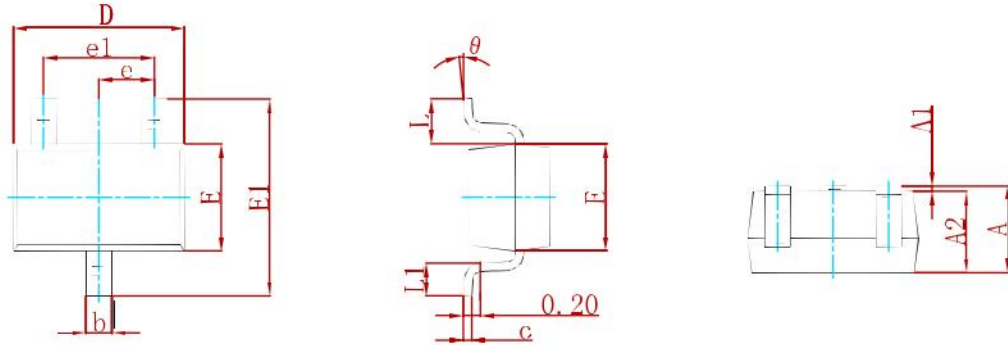


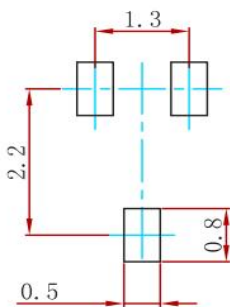
Fig.6 Maximum Safe Operation Area

PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018

Suggested Pad Layout



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
BSS138W-TP-MS	SOT-323	3000

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